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Notice of Allowability	Application No. Applicant(s)		
	10/766,188	MINE ET AL.	
Notice of Allowability	Examiner	Art Unit	
	Ngan Ngo	2814	
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.31	S (OR REMAINS) CLOSED i) or other appropriate comm RIGHTS. This application is	n this application. If not include unication will be mailed in due o	d course. THIS
1. This communication is responsive to			
2. ⊠ The allowed claim(s) is/are <u>1-20</u> .			
3. $igotimes$ The drawings filed on <u>29 January 2004</u> are accepted by the	ne Examiner.		
 4. Acknowledgment is made of a claim for foreign priority unally All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have all the priority documents have as a copies of the priority documents have as a copies of the certified copies of the priority documents have as a copies of the priority documents have a copies of the priority documents have as a copies of the priority documents have as a copies of the priority documents have a copies of th	e been received. The been received in Application ocuments have been received. The been received in Application ocuments have been received. The been received in Application to file of this application. The been received in Application ocupens in the been received in Application occurrence.	on No ed in this national stage applicat e a reply complying with the req AMINER'S AMENDMENT or No	uirements
 CORRECTED DRAWINGS (as "replacement sheets") mu (a) ☐ including changes required by the Notice of Draftsper 		w (PTO-948) attached	
1) ☐ hereto or 2) ☐ to Paper No./Mail Date	-		
(b) including changes required by the attached Examiner Paper No./Mail Date	's Amendment / Comment o	r in the Office action of	
Identifying indicia such as the application number (see 37 CFR each sheet. Replacement sheet(s) should be labeled as such in			back) of
 DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT 			lote the
Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☑ Notice of Draftperson's Patent Drawing Review (PTO-948)	6. 🗌 Interview S	nformal Patent Application (PTC Summary (PTO-413), ./Mail Date)-152)
 3. Information Disclosure Statements (PTO-1449 or PTO/SB/Paper No./Mail Date 0104 4. Examiner's Comment Regarding Requirement for Deposit of Biological Material 	08), 7. ⊠ Examiner's	s Amendment/Comment s Statement of Reasons for Allo	M,

Application/Control Number: 10/766,188

Art Unit: 2814

Examiner's Amendment

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

In the drawings:

Figures 7 and 8 are labeled "PRIOR ART". See MPEP 608.02(g).

Any inquiry concerning this communication should be directed to Examiner Ngan Ngo at telephone number (571) 272-1711. The fax number for the Art unit is (703) 308-7722.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist whose telephone number is (703) 308-0956.

Ngan Van Ngo Primary Examiner

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Ngan Ngo

7/30/04

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Reasons for Allowance

The following is an examiner's statement of reasons for allowance:

The prior arts of record do not teach the nonvolatile semiconductor memory device having "said charge trapping film comprises a silicon oxynitride film and a third insulator film in which the sum of the energy between a vacuum level and a conduction band of said third insulator film and a band gap of said third insulator film is smaller than that of said silicon oxynitride film; and wherein the product of a charge trap density and a film thickness of said silicon oxynitride film is larger than that of said third insulator film" in claim 1 and the "potential barrier film is 1 nm or less in thickness" in claim 18. The prior arts of record do not teach nonvolatile semiconductor memory device having only the potential barrier film and the silicon oxynitride film formed between the substrate and the gate electrode as claimed in claim 16

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Ngan Van Ngo Primary Examine